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PTO/SB/08A (08-00)

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Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham
Sheet	1	of	12	Attorney Docket Number	0756-7218

U.S. PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
PL		5,686,328		Zhang et al.	11/11/97	
		5,763,899		Yamazaki et al.	06/09/98	
		5,782,665		Weisfield et al.	07/21/98	
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		Japan J. Appl. Phys. 8 (1969) 1056, "Effect of Deposited Metals on the Crystallization Temperature of Amorphous Germanium Film," OKI et al.	
		Technology Information Association, "Thermo-Auto-Chrome Full Color Recording Technology," May 31, 1995	

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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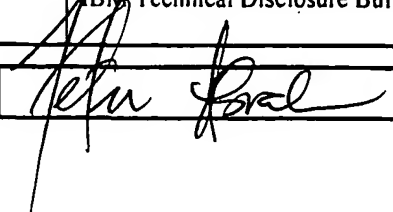
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		JP	07-335900		Teramoto Satoshi	12/22/95
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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✓		IBM Technical Disclosure Bulletin, Vol. 11, No.7, A.R. Baker, Jr.	

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		Wolf et al., "Silicon Processing for the VLSI Era Volume 1: Process Technology," 1986, pp. 198-207, Lattice Press	

Examiner Signature	<i>Fetsum Abraham</i>	Date Considered	2/8/05
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham
				Attorney Docket Number	0756-7218
Sheet	8	of	12		

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁴
7A		Thompson et al., "Silicide Formation in Pd-a-Si:H Schottky Barriers," August 1981, pp. 274-276, Appl. Phys. Lett., Vol. 39, No. 3	
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		Hayzelden et al., "Silicide Formation and Silicide Mediated Crystallization of Nickel-Implanted Amorphous Silicon Thin Films," May 15, 1993, pp. 8279-8289, J. Appl. Phys. 73(12)	

Examiner Signature	<i>Fetsum Abraham</i>	Date Considered	2/8/05
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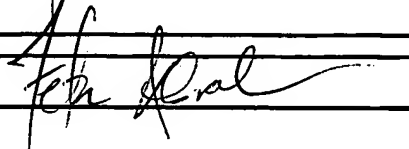
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham
Sheet	9	of	12	Attorney Docket Number	0756-7218

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
J		5,705,829		Miyanaga et al.	01/06/98	S
		5,712,191		Nakajima et al.	01/27/98	
		5,756,364		Tanaka et al.	05/26/98	
		5,619,044		Makita et al.	04/08/97	
		5,530,266		Yonehara et al.	06/25/96	
		5,550,070		Funai et al.	08/27/96	
		5,693,959		Inoue et al.	12/02/97	

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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		Kuznetsov et al., "Silicide Precipitate Formation and Solid Phase Re-Growth of Ni-Implanted Amorphous Silicon," April 5-8, 1993, pp. 191-194, Inst. Phys. Conf. Ser. No. 134.4: Proceedings of Royal Microscopical Society Conf.	
		Liu et al., "Polycrystalline Silicon Thin Film Transistors on Corning 7059 Glass Substrates Using Short Time, Low-Temperature Processing," May 17, 1993, pp. 2554-2556, Appl. Phys. Lett 62(20)	
		Liu et al., "Selective Area Crystallization of Amorphous Silicon Films by Low-Temperature Rapid Thermal Annealing," August 14, 1989, pp. 660-662, Appl. Phys. Lett 55(7)	
		Spaepen et al., Metal-Enhanced Growth of Silicon, 1992, pp. 483-499, Crucial Issues in Semiconductor Materials & Processing Technologies	

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		Number	Kind Code ³ (if known)			
Fetsum		5,403,772		Zhang et al.	04/04/95	
		5,426,064		Zhang et al.	06/20/95	
		5,481,121		Zhang et al.	01/02/96	
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		5,492,843		Adachi et al.	02/20/96	
		5,501,989		Takayama et al.	03/26/96	
		5,508,533		Takemura	04/16/96	
		5,529,937		Zhang et al.	06/25/96	
		5,534,716		Takemura	07/09/96	
		5,543,352		Ohtani et al.	08/06/96	
		5,563,426		Zhang et al.	10/08/96	
		5,569,610		Zhang et al.	10/29/96	
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		5,595,923		Zhang et al.	01/21/97	
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		5,614,426		Funada et al.	03/25/97	
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		5,646,424		Zhang et al.	07/08/97	
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		5,696,386		Yamazaki	12/09/97	
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		5,700,333		Yamazaki et al.	12/23/97	

Examiner Signature	<i>Fetsum</i>	Date Considered	8/30/01
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham
Sheet	11	of	12	Attorney Docket Number	0756-7218

U.S. PATENT DOCUMENTS					
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		Number	Kind Code ² (if known)		
FR		5,932,893		Miyanaga et al.	08/03/99
		4,759,610		Yanagisawa	07/26/88
		5,535,471		Guldi	07/16/96
		5,661,056		Takeuchi	08/26/97
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		5,210,050		Yamazaki et al.	05/11/93
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		5,313,076		Yamazaki et al.	05/17/94
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		5,372,860		Fehlner et al.	12/13/94
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		6,011,275		Ohtani et al.	01/04/00
		6,133,073		Yamazaki et al.	10/17/00

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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FR		Wolf, <i>Silicon Processing for the VLSI Era</i> , Volume 2, Chapter 4, page 274 (1990).	

Examiner Signature	<i>Fetsum Abraham</i>	Date Considered	8/30/05
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				Application Number	Based on 10/214,691	
Sheet		12	of	12	Filing Date	August 9, 2002
					First Named Inventor	Shunpei YAMAZAKI, et al.
					Group Art Unit	2826
					Examiner Name	Fetsum Abraham
					Attorney Docket Number	0756-7218

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		Number	Kind Code ² (if known)			
[Signature]		6,225,152	BI	Yamazaki et al.	05/01/01	[Wavy line]
		6,288,412	BI	Hamada et al.	09/11/01	
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		6,331,718	BI	Yamazaki et al.	12/18/01	

FOREIGN PATENT DOCUMENTS								
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		Office ³	Number ⁴	Kind Code ⁵ (if known)				
		JP	06-314785			11/08/94		Ab
		JP	06-314787			11/08/94		Ab

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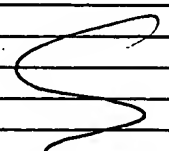
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary) NOV 15 2004 PATENT & TRADEMARK OFFICE		Application Number	10/712,062
		Filing Date	November 14, 2003
		First Named Inventor	Shunpei YAMAZAKI et al.
		Group Art Unit	2826
		Examiner Name	F. Abraham
		Attorney Docket Number	0756-7218
Sheet 1	2		

U.S. PATENT DOCUMENTS						
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		Number	Kind Code ² (if known)			
PR J		6,162,704		Yamazaki et al.	12/19/2000	
		6,294,441		Yamazaki	09/25/2001	
		6,461,943		Yamazaki et al.	10/08/2002	
		6,620,711		Yamazaki	09/16/2003	
		6,194,254		Takemura	02/27/2001	

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		Office ³	Number ⁴	Kind Code ⁵ (if known)				
Pr		JP	07-066425			03/10/1995		Abst. & U.S. Equiv.
		JP	08-045839			02/16/1996		Abst. & U.S. Equiv.
		JP	08-045840			02/16/1996		Abst. & U.S. Equiv.
		JP	08-097169			04/12/1996		Abst. & U.S. Equiv.
		KR	96-005879			02/23/1996		U.S. Equiv.
		JP	07-045519			02/14/1995		Abst. & U.S. Equiv.
		JP	07-231100			08/29/1995		Abst. & U.S. Equiv.
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/712,062
		Filing Date	November 14, 2003
		First Named Inventor	Shunpei YAMAZAKI et al.
		Group Art Unit	2826
		Examiner Name	F. Abraham
Sheet 2 of 2	of	Attorney Docket Number	0756-7218

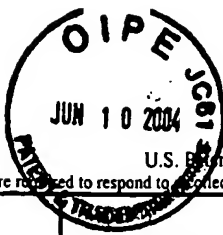
U.S. PATENT DOCUMENTS						
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		Number	Kind Code ² (if known)			
A		2002/0025659		Yamazaki et al.	02/28/2002	
		2002/0048891		Yamazaki et al.	04/25/2002	
		6,423,586		Yamazaki et al.	07/23/2002	

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		Office ³	Number ⁴	Kind Code ² (if known)				
JP		JP	07-192998			07/28/1995		Abst.
		JP	05-299339			11/12/1993		Abst. & U.S. Equiv.

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[Handwritten signature]		5,531,862		Otsubo et al.	07/02/1996	
		5,575,883		Nishikawa	11/19/1996	
		5,902,993		Okushiba et al.	05/11/1999	
		6,006,763		Mori et al.	12/28/1999	
		4,086,020		Tanabe et al.	04/25/1978	

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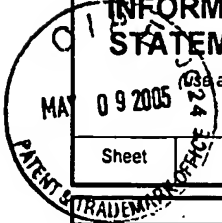
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				Filing Date	November 14, 2003
				First Named Inventor	Shunpei YAMAZAKI et al.
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